

Silicon carbide (SiC) slurries

Polishing slurries | **SiC substrate**

Vibrantz Technologies is pleased to announce the launch of our first-generation silicon carbide (SiC) slurry. The semiconductor industry is accelerating alongside electric vehicles (EVs), and our new acidic formulation satisfies the market demand for superior SiC wafer polishing solutions.

Our new acidic-permanganate slurry is designed for single passes that accomplish exceptional surface finishes combined with impressive removal rates (RR). We are proud to share our latest performance data, which achieves surface finishes between 0.7 and 0.8 angstroms with RR as high as 7 micrometers per hour.

Key benefits and features

- Mix and polish with no pre-polish pH adjustments required
- Low particle and scratch defectivity counts
- Enhanced polishing precision and efficiency



Product performance

Removal rate (RR)	4.5-7 $\mu\text{m/hr}$
Si-face to C-face RR ratio	1:3.5
Surface finish	0.7-0.8 \AA
Total useable area percentage	Up to 99%

Physical properties

Appearance	Purple liquid
Density	1.02 g/ml
Lbs/gal	8.48
pH	4.25
Percent solids	3%